### SN65C1406, SN75C1406 TRIPLE LOW-POWER DRIVERS/RECEIVERS

SLLS148E - MAY 1990 - REVISED OCTOBER 2001

- Meet or Exceed the Requirements of TIA/EIA-232-F and ITU Recommendation V.28
- Very Low Power Consumption . . .5 mW Typ
- Wide Driver Supply Voltage Range . . . ±4.5 V to ±15 V
- Driver Output Slew Rate Limited to 30 V/μs Max
- Receiver Input Hysteresis . . . 1000 mV Typ
- Push-Pull Receiver Outputs
- On-Chip Receiver 1-μs Noise Filter
- Functionally Interchangeable With Motorola MC145406 and Texas Instruments TL145406
- Package Options Include Plastic Small-Outline (D, DW, NS) Packages and DIPs (N)

#### SN65C1406 . . . D PACKAGE SN75C1406 . . . D, DW, N, OR NS PACKAGE (TOP VIEW) V<sub>DD</sub> L 16 VCC 1RA **∏** 2 15**∏** 1RY 1DY **∏** 3 14**∏** 1DA 2RA 🛮 4 13 2RY 2DY 🛮 5 12 **□** 2DA 11 3RY 3RA **∏** 6 10**∏** 3DA 3DY **1** 7 9 GND V<sub>SS</sub> 🛛 8

#### description

The SN65C1406 and SN75C1406 are low-power BiMOS devices containing three independent drivers and receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). These devices are designed to conform to TIA/EIA-232-F. The drivers and receivers of the SN65C1406 and SN75C1406 are similar to those of the SN75C188 quadruple driver and SN75C189A quadruple receiver, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ $\mu$ s, and the receivers have filters that reject input noise pulses shorter than 1  $\mu$ s. Both these features eliminate the need for external components.

The SN65C1406 and SN75C1406 are designed using low-power techniques in a BiMOS technology. In most applications, the receivers contained in these devices interface to single inputs of peripheral devices such as ACEs, UARTs, or microprocessors. By using sampling, such peripheral devices are usually insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN65C1406 and SN75C1406 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

The SN65C1406 is characterized for operation from  $-40^{\circ}$ C to  $85^{\circ}$ C. The SN75C1406 is characterized for operation from  $0^{\circ}$ C to  $70^{\circ}$ C.

#### AVAILABLE OPTIONS

		PACKAGED DEVICES								
TA	SMALL OUTLINE (D)	SMALL OUTLINE (DW)	PLASTIC DIP (N)	PLASTIC SMALL OUTLINE (NS)						
-40°C to 85°C	SN65C1406D									
0°C to 70°C	SN75C1406D	SN75C1406DW	SN75C1406N	SN75C1406NS						

The D, DW, and PW packages are available taped and reeled. Add the suffix R to device type (e.g., SN75C1406DR).



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## logic diagram (positive logic)

Typical of Each Receiver

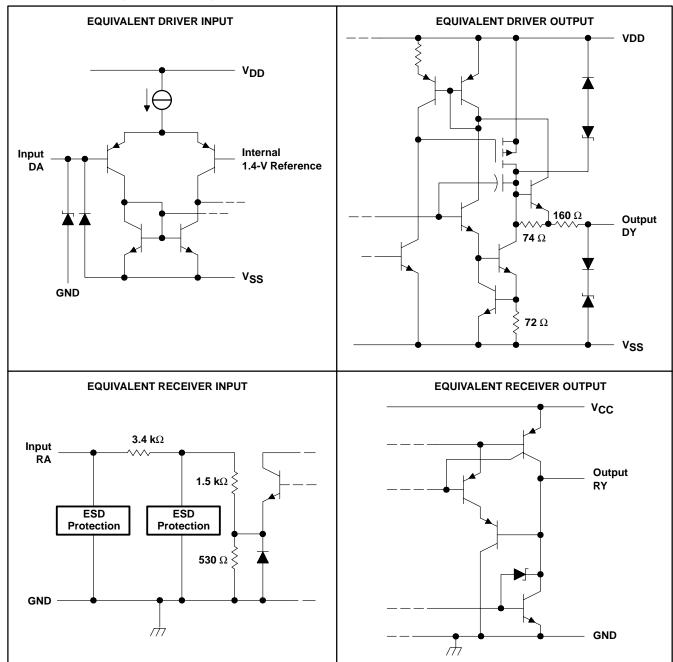


**Typical of Each Driver** 





## schematics of inputs and outputs



All resistor values shown are nominal.

## SN65C1406, SN75C1406 TRIPLE LOW-POWER DRIVERS/RECEIVERS

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absolute maximum ratings over operating	free-air temperature ra	ange (unless otherwise noted)†
Supply voltage: V <sub>DD</sub> (see Note 1)		
V <sub>SS</sub>		
V <sub>CC</sub>		
Input voltage range, V <sub>I</sub> : Driver		
Receiver		
Output voltage range, VO: Driver		$(V_{SS} - 6 \text{ V})$ to $(V_{DD} + 6 \text{ V})$
Receiver		$-0.3 \text{ V to } (V_{CC} + 0.3 \text{ V})$
Package thermal impedance, $\theta_{JA}$ (see Note	2): D package	
	DW package	57°C/W
	N package	67°C/W
	NS package	64°C/W
Lead temperature 1,6 mm (1/16 inch) from c	ase for 10 seconds	260°C
Storage temperature range, T <sub>stg</sub>		

#### recommended operating conditions

			MIN	NOM	MAX	UNIT		
$V_{DD}$	Supply voltage		4.5	12	15	V		
VSS	Supply voltage		-4.5	-12	-15	V		
VCC	Supply voltage		4.5	5	6	V		
Vi	Input voltage	Driver	V <sub>SS</sub> +2		$V_{DD}$	V		
٧١	input voltage	Receiver			±25			
VIH	High-level input voltage		2			V		
VIL	Low-level input voltage				0.8	V		
IOH	High-level output current				-1	mA		
loL	Low-level output curren				3.2	mA		
т.	Operating free-air temperature	SN65C1406	-40		85	°C		
Тд	Operating nee-all temperature	SN75C1406	0		70	C		



<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to the network ground terminal.

<sup>2.</sup> The package thermal impedance is calculated in accordance with JESD 51-7.

#### **DRIVER SECTION**

# electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10% (unless otherwise noted)

	PARAMETER		TEST CON	DITIONS		MIN	TYP <sup>†</sup>	MAX	UNIT
\/ <b>-</b>	Lligh lovel output voltage	V <sub>IH</sub> = 0.8 V,	$R_L = 3 \text{ k}\Omega$ ,	$V_{DD} = 5 V$	V <sub>SS</sub> = -5 V	4	4.5		V
VOH	High-level output voltage	See Figure 1		V <sub>DD</sub> = 12 V,	V <sub>SS</sub> = -12 V	10	10.8		V
Vai	Low-level output voltage	V <sub>IH</sub> = 2 V,	$R_L = 3 k\Omega$ ,	$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		-4.4	-4	V
VOL	(see Note 3)	See Figure 1		$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$		-10.7	-10	V
lН	High-level input current	V <sub>I</sub> = 5 V,	See Figure 2					1	μΑ
IլL	Low-level input current	$V_{I} = 0,$	See Figure 2					-1	μΑ
los(H)	High-level short-circuit output current <sup>‡</sup>	V <sub>I</sub> = 0.8 V,	$V_O = 0$ or $V_{SS}$ ,	See Figure 1		-7.5	-12	-19.5	mA
los(L)	Low-level short-circuit output current <sup>‡</sup>	V <sub>I</sub> = 2 V,	$V_O = 0$ or $V_{DD}$ ,	See Figure 1		7.5	12	19.5	mA
	Supply current from VDD	No load,		$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		115	250	^
lDD	Supply current from VDD	All inputs at 2	V or 0.8 V	$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$		115	250	μΑ
laa	Supply ourrant from \/aa	No load,		$V_{DD} = 5 V$ ,	$V_{SS} = -5 V$		-115	-250	^
ISS	Supply current from VSS	All inputs at 2	V or 0.8 V	$V_{DD} = 12 V$ ,	$V_{SS} = -12 \text{ V}$		-115	-250	μΑ
rO	Output resistance	V <sub>DD</sub> = V <sub>SS</sub> = See Note 4	V <sub>CC</sub> = 0,	$V_0 = -2 \text{ V to}$	2 V,	300	400		Ω

<sup>&</sup>lt;sup>†</sup> All typical values are at  $T_A = 25$ °C.

NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only.

4. Test conditions are those specified by TIA/EIA-232-F.

## switching characteristics at $T_A$ = 25°C, $V_{DD}$ = 12 V, $V_{SS}$ = –12 V, $V_{CC}$ = 5 V $\pm$ 10%

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output§	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 15 pF, See Figure 3		1.2	3	μs
tPHL	Propagation delay time, high- to low-level output§	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 15 pF, See Figure 3		2.5	3.5	μs
tTLH	Transition time, low- to high-level output¶	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 15 pF, See Figure 3	0.53	2	3.2	μs
tTHL	Transition time, high- to low-level output¶	R <sub>L</sub> = 3 k $\Omega$ to 7 k $\Omega$ , C <sub>L</sub> = 15 pF, See Figure 3	0.53	2	3.2	μs
tTLH	Transition time, low- to high-level output#	R <sub>L</sub> = 3 k $\Omega$ to 7 k $\Omega$ , C <sub>L</sub> = 2500 pF, See Figure 3		1	2	μs
tTHL	Transition time, high- to low-level output#	$R_L$ = 3 kΩ to 7 kΩ, $C_L$ = 2500 pF, See Figure 3		1	2	μs
SR	Output slew rate	R <sub>L</sub> = 3 kΩ to 7 kΩ, C <sub>L</sub> = 15 pF, See Figure 3	4	10	30	V/μs

<sup>\$</sup> tPHL and tPLH include the additional time due to on-chip slew rate and are measured at the 50% points.



<sup>‡</sup> Not more than one output should be shorted at a time.

Measured between 10% and 90% points of output waveform

<sup>#</sup> Measured between 3-V and -3-V points of output waveform (TIA/EIA-232-F conditions) with all unused inputs tied either high or low

#### RECEIVER SECTION

# electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10% (unless otherwise noted)

	PARAMETER		TEST CO	NDITIONS	MIN	TYP†	MAX	UNIT
VIT+	Positive-going input threshold voltage	See Figure 5			1.7	2	2.55	V
V <sub>IT</sub> _	Negative-going input threshold voltage	See Figure 5			0.65	1	1.25	V
V <sub>hys</sub>	Input hysteresis voltage (V <sub>IT+</sub> -V <sub>IT-</sub> )				600	1000		mV
		V <sub>I</sub> = 0.75 V,	$I_{OH} = -20 \mu A$ ,	See Figure 5 and Note 5	3.5			
\/a	High-level output voltage	.,		V <sub>CC</sub> = 4.5 V	2.8	4.4		v
VOH	High-level output voltage	V <sub>I</sub> = 0.75 V, See Figure 5	$I_{OH} = -1 \text{ mA},$	V <sub>CC</sub> = 5 V	3.8	4.9		V
		Gee rigule o		V <sub>CC</sub> = 5.5 V	4.3	5.4		
VOL	Low-level output voltage	V <sub>I</sub> = 3 V,	$I_{OL} = 3.2 \text{ mA},$	See Figure 5		0.17	0.4	V
I	High-level input current	V <sub>I</sub> = 2.5 V			3.6	4.6	8.3	mA
ΊΗ	nign-level input current	V <sub>I</sub> = 3 V			0.43	0.55	1	ША
1	Low-level input current	$V_{I} = -2.5 V$			-3.6	<b>–</b> 5	-8.3	mA
lIL.	Low-level input current	$V_{I} = -3 V$			-0.43	-0.55	-1	ША
los(H)	High-level short-circuit output current	V <sub>I</sub> = 0.75 V,	$V_{O} = 0$ ,	See Figure 4		-8	-15	mA
IOS(L)	Low-level short-circuit output current	VI = VCC,	$V_O = V_{CC}$	See Figure 4		13	25	mA
loo	Supply current from V <sub>CC</sub>	No load,		$V_{DD} = 5 \text{ V},  V_{SS} = -5 \text{ V}$		320	450	
Icc	Supply carrent none vCC	All inputs at 0 o	r 5 V	$V_{DD} = 12 \text{ V},  V_{SS} = -12 \text{ V}$		320	450	μΑ

<sup>&</sup>lt;sup>†</sup> All typical values are at  $T_A = 25$ °C.

NOTE 5: If the inputs are left unconnected, the receiver interprets this as an input low and the receiver outputs remain in the high state.

## switching characteristics at $T_A$ = 25°C, $V_{DD}$ = 12 V, $V_{SS}$ = -12 V, $V_{CC}$ = 5 V $\pm$ 10% (unless otherwise noted)

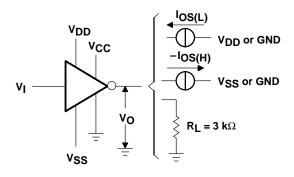
	PARAMETER	TEST CO	NDITIONS	MIN	TYP	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	C <sub>L</sub> = 50 pF, See Figure 6	$R_L = 5 k\Omega$ ,		3	4	μs
<sup>t</sup> PHL	Propagation delay time, high- to low-level output	C <sub>L</sub> = 50 pF, See Figure 6	$R_L = 5 k\Omega$ ,		3	4	μs
tTLH	Transition time, low- to high-level output <sup>‡</sup>	C <sub>L</sub> = 50 pF, See Figure 6	$R_L = 5 \text{ k}\Omega$ ,		300	450	ns
tTHL	Transition time, high- to low-level output <sup>‡</sup>	C <sub>L</sub> = 50 pF, See Figure 6	R <sub>L</sub> = 5 kΩ,		100	300	ns
t <sub>w</sub> (N)	Duration of longest pulse rejected as noise§	$C_L = 50 pF$ ,	R <sub>L</sub> = 5 kΩ	1		4	μs

<sup>&</sup>lt;sup>‡</sup> Measured between 10% and 90% points of output waveform



<sup>§</sup> The receiver ignores any positive- or negative-going pulse that is less than the minimum value of  $t_{W(N)}$  and accepts any positive- or negative-going pulse greater than the maximum of  $t_{W(N)}$ .

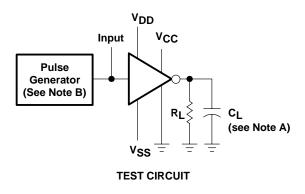
#### PARAMETER MEASUREMENT INFORMATION

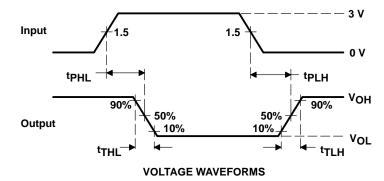


V<sub>I</sub> — V<sub>DD</sub> V<sub>CC</sub> V<sub>CC</sub> V<sub>SS</sub>

Figure 1. Driver Test Circuit V<sub>OH</sub>, V<sub>OL</sub>, I<sub>OS(L)</sub>, I<sub>OS(H)</sub>

Figure 2. Driver Test Circuit, I<sub>IL</sub>, I<sub>IH</sub>

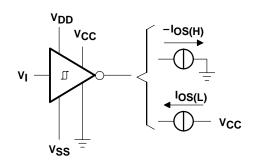




NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $t_W$  = 25  $\mu$ s, PRR = 20 kHz,  $Z_O$  = 50  $\Omega$ ,  $t_f$  =  $t_f$  < 50 ns.

Figure 3. Driver Test Circuit and Voltage Waveforms



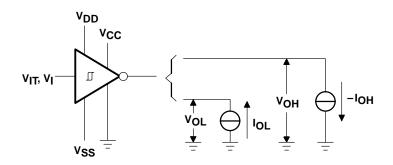
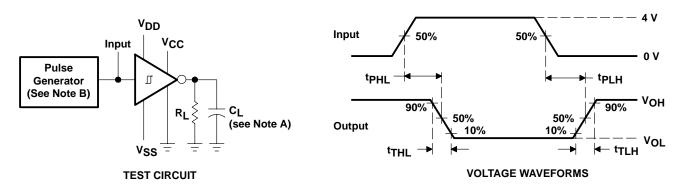


Figure 4. Receiver Test Circuit, IOS(H), IOS(L)

Figure 5. Receiver Test Circuit,  $V_{IT}$ ,  $V_{OL}$ ,  $V_{OH}$ 

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#### PARAMETER MEASUREMENT INFORMATION



NOTES: C. C<sub>I</sub> includes probe and jig capacitance.

D. The pulse generator has the following characteristics:  $t_W = 25 \mu s$ , PRR = 20 kHz,  $Z_Q = 50 \Omega$ ,  $t_f = t_f < 50 ns$ .

Figure 6. Receiver Test Circuit and Voltage Waveforms

#### **APPLICATION INFORMATION**

The TIA/EIA-232-F specification is for data interchange between a host computer and a peripheral at signaling rates up to 20 kbit/s. Many TIA/EIA-232-F devices will operate at higher data rates with lower capacitive loads (short cables). For reliable operation at greater than 20 kbit/s, the designer needs to have control of both ends of the cable. By mixing different types of TIA/EIA-232-F devices and cable lengths, errors can occur at higher frequencies (above 20 kbit/s). When operating within the TIA/EIA-232-F requirements of less than 20 kbit/s and with compliant line circuits, interoperability is assured. For applications operating above 20 kbit/s, the design engineer should consider devices and system designs that meet the TIA/EIA-232-F requirements.



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#### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C1406D	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1406	Samples
SN65C1406DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C1406	Samples
SN75C1406D	ACTIVE	SOIC	D	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1406	Samples
SN75C1406DR	ACTIVE	SOIC	D	16	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1406	Samples
SN75C1406DW	ACTIVE	SOIC	DW	16	40	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1406	Samples
SN75C1406DWR	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1406	Samples
SN75C1406N	ACTIVE	PDIP	N	16	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	SN75C1406N	Samples
SN75C1406NSR	ACTIVE	SO	NS	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	SN75C1406	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



## **PACKAGE OPTION ADDENDUM**

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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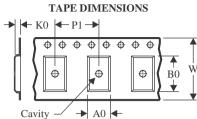
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## **PACKAGE MATERIALS INFORMATION**

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#### TAPE AND REEL INFORMATION





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A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C1406DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75C1406DR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
SN75C1406DWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
SN75C1406NSR	so	NS	16	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1



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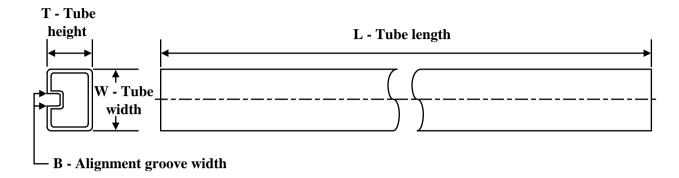
#### \*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C1406DR	SOIC	D	16	2500	340.5	336.1	32.0
SN75C1406DR	SOIC	D	16	2500	340.5	336.1	32.0
SN75C1406DWR	SOIC	DW	16	2000	350.0	350.0	43.0
SN75C1406NSR	SO	NS	16	2000	356.0	356.0	35.0

## **PACKAGE MATERIALS INFORMATION**

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#### **TUBE**



\*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65C1406D	D	SOIC	16	40	507	8	3940	4.32
SN75C1406D	D	SOIC	16	40	507	8	3940	4.32
SN75C1406DW	DW	SOIC	16	40	506.98	12.7	4826	6.6
SN75C1406N	N	PDIP	16	25	506	13.97	11230	4.32



SOP



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.



SOF



#### NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOF



#### NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



## D (R-PDS0-G16)

#### PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.



#### **MECHANICAL DATA**

## NS (R-PDSO-G\*\*)

## 14-PINS SHOWN

#### PLASTIC SMALL-OUTLINE PACKAGE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





SOIC



- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



SOIC



#### NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



#### NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



## N (R-PDIP-T\*\*)

## PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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